

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Application Number		10582390
	Filing Date		2010-04-17
	First Named Inventor	Michael D. Craven	
	Art Unit	2818	
	Examiner Name	Brandon C. Fox	
	Attorney Docket Number	30794104USWO	

U.S.PATENTS						Remove
Examiner Initial*	Cite No	Patent Number	Kind Code ¹	Issue Date	Name of Patentee or Applicant of cited Document	Pages,Columns,Lines where Relevant Passages or Relevant Figures Appear
	1					

If you wish to add additional U.S. Patent citation information please click the Add button.

Add

U.S.PATENT APPLICATION PUBLICATIONS						Remove
Examiner Initial*	Cite No	Publication Number	Kind Code ¹	Publication Date	Name of Patentee or Applicant of cited Document	Pages,Columns,Lines where Relevant Passages or Relevant Figures Appear
	1	20020098641		2002-07-25	Tsuda, et al.	
	2	20030198837		2003-10-23	Craven et al.	

If you wish to add additional U.S. Published Application citation information please click the Add button.

Add

FOREIGN PATENT DOCUMENTS								Remove
Examiner Initial*	Cite No	Foreign Document Number ³	Country Code ²	Kind Code ⁴	Publication Date	Name of Patentee or Applicant of cited Document	Pages,Columns,Lines where Relevant Passages or Relevant Figures Appear	T ⁵
	1							<input type="checkbox"/>

If you wish to add additional Foreign Patent Document citation information please click the Add button

Add

NON-PATENT LITERATURE DOCUMENTS								Remove
---------------------------------	--	--	--	--	--	--	--	--------

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Application Number		10582390
	Filing Date		2010-04-17
	First Named Inventor	Michael D. Craven	
	Art Unit	2818	
	Examiner Name	Brandon C. Fox	
	Attorney Docket Number	30794104USWO	

Examiner Initials*	Cite No	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, pages(s), volume-issue number(s), publisher, city and/or country where published.	T ⁵
	1	JP Office Action 12/7/10 (Application No. 2005-512863) with translation.	<input type="checkbox"/>
	2	EP Search Report dated 1/12/11 (Application No. 03790447).	<input type="checkbox"/>
	3	CRAVEN, Michael D., et. al., "Characterization of a-plane GaN/(Al,Ga)N multiple quantum wells grown via metalorganic chemical vapor deposition", JAPANESE JOURNAL OF APPLIED PHYSICS, PART 2 (LETTERS) JAPAN SOC. APPL. PHYS. JAPAN, vol. 42, no. 3A, March 1, 2003, pages L235-L238, XP002614887.	<input type="checkbox"/>
	4	CHEN, Changqing et. al., "Ultraviolet light emitting diodes using non-polar a-plane GaN-AlGaIn multiple quantum wells", JAPANESE JOURNAL OF APPLIED PHYSICS, PART 2 (LETTERS) JAPAN SOC. APPL. PHYS. JAPAN, vol. 42, no. 9AB, September 15, 2003, pages L1039-L1040, XP002614886.	<input type="checkbox"/>
	5	KUOKSTIS, E., et al., "Polarization effects in photoluminescence of C- and M-plane GaN/AlGaIn multiple quantum wells", APPLIED PHYSICS LETTERS, AIP, AMERICAN INSTITUTE OF PHYSICS, Melville, NY, US., vol. 81, no. 22, November 25, 2002, pages 4130-4132, XP012032618.	<input type="checkbox"/>
	6	NG, H.M., "Molecular-beam epitaxy of GaN/Al _x Ga _{1-x} N multiple quantum wells on R-plane (1012) sapphire substrates", APPLIED PHYSICS LETTERS, AIP, AMERICAN INSTITUTE OF PHYSICS, Melville, NY, vol. 80, no. 23, June 10, 2002, pages 4369-4371, XP012031145, ISSN: 0003-6951.	<input type="checkbox"/>
	7	SUN, W.H., et al., "Strong ultraviolet emission from non-polar AlGaIn/GaN quantum wells grown over r-plane sapphire substrates", PHYSICA STATUS SOLIDI A WILEY-VCH GERMANY, vol. 200, no. 1, November 2003, pages 48-51, XP002614885, ISSN: 0031-8965.	<input type="checkbox"/>

If you wish to add additional non-patent literature document citation information please click the Add button

EXAMINER SIGNATURE

Examiner Signature	Date Considered
--------------------	-----------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through a citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ See Kind Codes of USPTO Patent Documents at www.USPTO.GOV or MPEP 901.04. ² Enter office that issued the document, by the two-letter code (WIPO Standard ST.3). ³ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁴ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁵ Applicant is to place a check mark here if English language translation is attached.